

Gauss' Law:

$$\frac{dE}{dx} = \frac{\rho}{\epsilon}$$

if $\rho = 0 \Rightarrow E = 0$

for example: capacitor



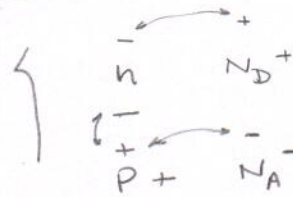
there is no need to have ρ at the same location of E .

Uniformly-doped semiconductor in T.E:

In the bulk:

charge neutrality: $\rho = 0$

$\therefore E$ cannot change in space
($dE/dx = 0$)

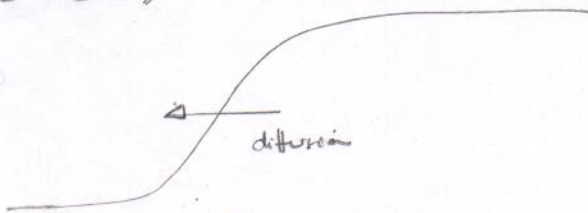


no electric field applied $\Rightarrow E = 0$

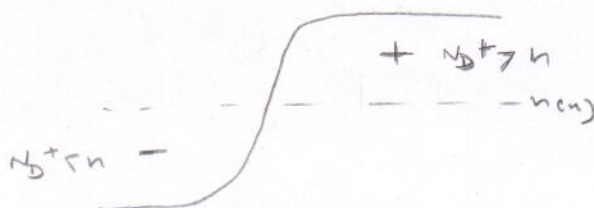
Non-uniformly-doped semiconductor in T.E:

n-type:
$$\frac{dE_0}{dx} = \frac{q}{\epsilon} (N_D - n_0)$$

① if $n(x) = N_D(x) \Rightarrow$ charge neutrality at every single point.



② electrons will flow until $n(x)$ is uniform:



$\Rightarrow$ pull electrons back

$$\Rightarrow n(x) \neq N_D(x)$$

Using the following expressions:

1) Gauss' Law :

divergence of the electric field is proportional to the volume charge density:

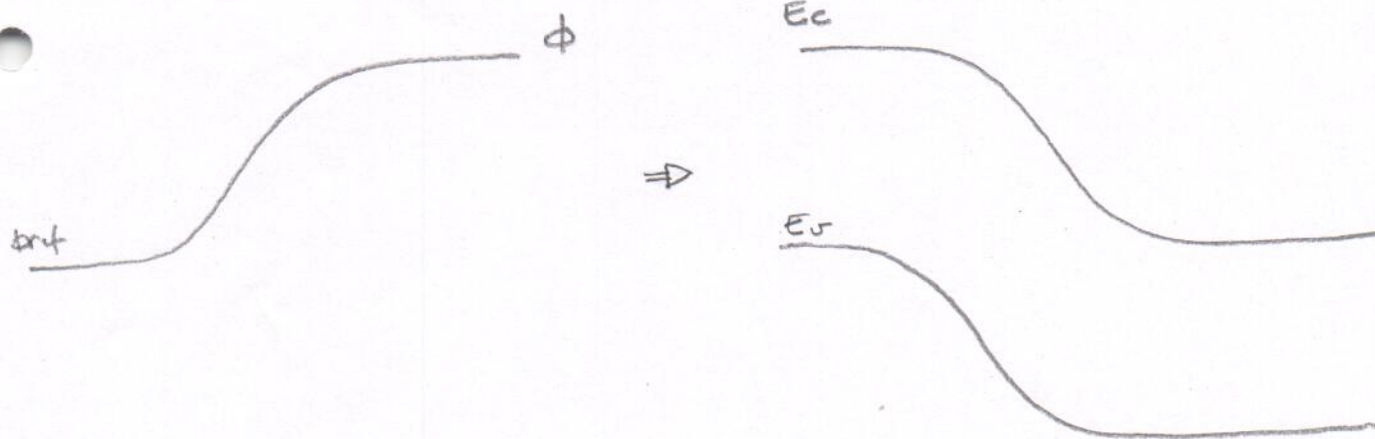
$$\frac{dE}{dx} = \frac{\rho}{\epsilon}$$

2) $\frac{d\phi}{dx} = -E \Rightarrow$ electric field creates a derivative of potential.

3) In an arbitrary reference : $E_c + E_{ref} = E_p = -q \cdot \phi$

thus : $E = -\frac{d\phi}{dx} = \frac{1}{q} \frac{dE_c}{dx} = \frac{1}{q} \frac{dE_v}{dx}$

the shape of the band structure reflects the shape of the electric potential inverted.



* In TE, $J_e = 0$:

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$$J_e = \underbrace{q \cdot \mu_e \cdot n_0 E_0}_{\text{drift}} + \underbrace{q \cdot D_e \cdot \frac{dn_0}{dx}}_{\text{diffusion}} = 0$$

drift diffusion in perfect balance.

$$E_0 = - \frac{D_e}{\mu_e} \cdot \frac{1}{n_0} \cdot \frac{dn_0}{dx}$$

$\Rightarrow$
Einstein
relation

$$\left\{ \begin{array}{l} E_0 = - \frac{kT}{q} \cdot \frac{1}{n_0} \cdot \frac{dn_0}{dx} \\ E_0 = + \frac{kT}{q} \cdot \frac{1}{p_0} \cdot \frac{dp_0}{dx} \end{array} \right.$$

$\Rightarrow$ same result can
be obtained using

$$n_0 p_0 = n_i^2$$

if we know $n_0, p_0 \Rightarrow E_0 \Rightarrow \phi_0 \Rightarrow$

In T.E, there is a
direct connection between
equilibrium carrier concentration
and electric field.

$$E_0 = - \frac{d\phi_0}{dx} = - \frac{kT}{q} \cdot \frac{1}{n_0} \cdot \frac{dn_0}{dx}$$

$$\frac{d\phi_0}{dx} = \frac{kT}{q} \cdot \frac{d \ln(n_0)}{dx}$$

$$\phi_0(x) - \phi(\text{ref}) = \frac{kT}{q} \cdot \ln \left(\frac{n_0(x)}{n_0(\text{ref})} \right)$$

* cont

One possible reference point: $\phi(\text{ref}) = 0 \quad n_0(\text{ref}) = n_i$

$$\boxed{\phi_0(x) = \frac{kT}{q} \cdot \ln \frac{n_0(x)}{n_i}}$$

$$\left\{ \begin{array}{l} n_0 = n_i \cdot \exp \left(\frac{q \phi_0(x)}{kT} \right) \\ p_0 = n_i \cdot \exp \left(- \frac{q \phi_0(x)}{kT} \right) \end{array} \right.$$

$\Rightarrow n \propto e^{-E_p/kT}$ applies also to molecules in
the atmosphere; subject to gravitational forces.

$\Rightarrow$ atmosphere gets thinner as we
go UP.

$$E_p = -q \cdot \phi_0(x)$$

Boltzmann Relations

$\Downarrow$

fundamental law of
statistical mechanics

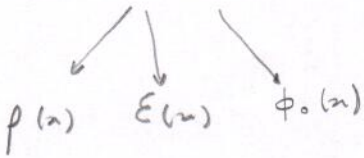
$$n \propto e^{-E_p/kT}$$

$$\frac{d\epsilon_0}{dx} = \frac{q}{\epsilon} (N_D - n_0)$$

$$\frac{d}{dx} \left(-\frac{kT}{q} \cdot \frac{d}{dx} \ln(n_0) \right) = \frac{q}{\epsilon} (N_D - n_0)$$

$$\frac{\epsilon \cdot kT}{q^2} \cdot \frac{d^2}{dx^2} \ln(n_0) = N_D - n_0$$

Solution of this second-order non-linear differential equation gives $\underline{n_0(x)}$, however this is NOT a simple equation.



Quasi - Fermi levels

In T.E. :

E_F is constant and precisely defines n, p

non-degenerate case:

$$\begin{cases} n_0 = N_C \exp\left(\frac{E_F - E_C}{kT}\right) \\ p_0 = N_V \exp\left(\frac{E_V - E_F}{kT}\right) \end{cases}$$

a single E_F

Out of Equilibrium :

$$n \neq n_0$$

$$p \neq p_0$$

$\therefore$ cannot find a single value of E_F

$\Rightarrow$ Define 2 quasi-Fermi levels: $\begin{cases} E_{F_c} \\ E_{F_v} \end{cases}$

for non-degenerate:

$$\begin{cases} n = N_C \exp\left(\frac{E_{F_c} - E_C}{kT}\right) \\ p = N_V \exp\left(\frac{E_V - E_{F_v}}{kT}\right) \end{cases}$$

$\Rightarrow$ Visualization tool: n directly related to the distance of E_{F_c} to E_C

$$n \cdot p = n_i^2 \exp\left(\frac{E_{F_c} - E_{F_v}}{kT}\right)$$

Let's explore:

$$n = N_c \cdot \exp\left(\frac{E_{Fe} - E_c}{kT}\right)$$

$$\begin{aligned}\frac{dn}{dx} &= \frac{n}{kT} \cdot \left(\frac{dE_{Fe}}{dx} - \frac{dE_c}{dx} \right) \\ &= \frac{n}{kT} \cdot \left(\frac{dE_{Fe}}{dx} - q \cdot \mathcal{E} \right)\end{aligned}$$

$$\mathcal{E} = -\frac{d\phi}{dx}$$

$$\mathcal{E} = \frac{1}{q} \cdot \frac{dE_c}{dx}$$

Calculate current:

$$\begin{aligned}J_e &= q \mu_e \cdot n \cdot \mathcal{E} + q D_e \frac{dn}{dx} \\ &= q \mu_e \cdot n \cdot \mathcal{E} + q \cdot D_e \cdot \frac{n}{kT} \cdot \frac{dE_{Fe}}{dx} - \underbrace{\frac{q^2 \cdot n \cdot D_e}{kT} \mathcal{E}}_{q \cdot n \cdot \mu_e \cdot \mathcal{E}}\end{aligned}$$

but $\frac{D_e}{\mu_e} = \frac{kT}{q}$

$$\begin{cases} J_e = \frac{q \cdot D_e}{kT} \cdot n \cdot \frac{dE_{Fe}}{dx} = n \cdot \mu_e \cdot \frac{dE_{Fe}}{dx} \\ J_h = \mu_h \cdot p \cdot \frac{dE_{Fh}}{dx} \end{cases}$$

$\therefore$ Gradient of quasi-Fermi levels unified driving force for carrier flow as it combines drift and diffusion.

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$$kT \mu_e \frac{dE_{Fe}}{dx} = q \cdot \mu_e \cdot \mathcal{E}$$

$$\frac{dE_{Fe}}{dx} = -\frac{q \cdot \mathcal{E}}{\mu_e}$$

$\Rightarrow$ if E_{Fe} is flat $\Rightarrow \mathcal{E} = 0$

$\Rightarrow$ if E_{Fe} has slope $\Rightarrow$ carriers are flowing

$$\frac{dE_{Fh}}{dx} = \frac{q \cdot \mathcal{E}}{\mu_h}$$

- while recombination is happening, electrons are nearly in equilibrium with lattice
 - Not in equilibrium with holes
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$$n \cdot p = n_i^2 \cdot \exp\left(\frac{E_{fc} - E_{fh}}{kT}\right)$$

if E_{fc} is above $E_{fh} \Rightarrow n \cdot p > n_i^2 \Rightarrow$ recombination prevails

else, E_{fc} is below $E_{fh} \Rightarrow n \cdot p < n_i^2 \Rightarrow$ generation prevails.